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4717-13300

APPLICATION NO.:

10/809,918

APPLICANT:

C. Maleville et al.

FILING DATE:

March 26, 2004

GROUP:

2812 2824

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
BE0	AA	4,743,767	5/1988	Plumb et al.	250	492.2	
BE0	AB	4,751,393	6/1988	Corey, Jr. et al.	250	492.21	
BE0	AC	4,807,994	2/1989	Felch et al.	356	326	
BE0	AD	5,374,564	12/1994	Bruel	437	24	
	AE	5,834,463	11/1998	Ohkawa et al.	514	220	
BE0	AF	5,998,798	12/1999	Halling et al.	250	492.21	

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	AG							
	AH							
	AI							

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

BE0	AJ	Scott M. Baumann, "Rutherford Backscattering Spectrometry (RBS), Charles Evans & Associates, Specialists in Materials Characterization, pp. 1-15.
	AK	
	AL	
	AM	
	AN	
	AO	

EXAMINER

DATE CONSIDERED

B. E. Owens

9.13.04

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

				ATTY DOCKET NO 4717-13300		APPLICATION NO 10/809,918	
				APPLICANT C. Maleville et al.			
				FILING DATE March 26, 2004		GROUP 2812	
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Beo	AA	760 409	6/1998	Chen et al.	250	492.21	
	AB	Beo 9.17.04					
	AC						
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
Beo	AD	JP 61 043417 A English Abstract	3/1986	Japan	250		X
Beo	AE	WO 99 08307 A	2/1999	PCT			X
	AF						
<b>OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
Beo	AG	Shirotekate et al., XP004195210, "Dose and implantation temperature influence extended defects nucleation in c-Si", Nuclear instruments and methods in physics research, section B: beam interactions with materials and atoms, North-Holland Publishing Company, Vol. 164-165, pp. 425-430 (2000)					
Beo	AH	L.J. Huang et al., XP000905645, "Model for blistering of hydrogen implanted silicon and its application to silicon-on-quartz", Electrochemical Society Proceedings, Processing of 8th International Symposium on Semiconductor Silicon Vol 98-1, pp. 1373-1384 (1998)					
	AI	Da Silva et al., XP004242656, "The effects of implantation temperature on He bubble formation in silicon", Nuclear instrument and methods in physics research, section B: beam interactions with materials and atoms, North-Holland Publishing Company, Amsterdam, NL, Vol. 175-177, pp. 335-339 (2001)					
Beo	AJ	Bruehl et al., XP000611125, "Application of Hydrogen Ion Beams To Silicon on Insulator Material Technology", Nuclear instrument and methods in physics research, section B: beam interactions with materials and atoms, North-Holland Publishing Company, Amsterdam, NL, Vol. 108, No. 3, pp. 313-319 (1996)					
Beo	AK	Lanzieri et al., XP000073904 "Activation Uniformity Improvement of Undoped semi-insulating Gaas with an improved Post-Implant Anneal Furnace", Journal of applied Physics, New York, Vol. 66, No. 8, pp 3643-3644 (1989) Beo 9.17.04					
EXAMINER Bren E. Owens				DATE CONSIDERED 9.17.04			